

UP0411x Series

Silicon PNP epitaxial planar type

For switching/digital circuits

■ Features

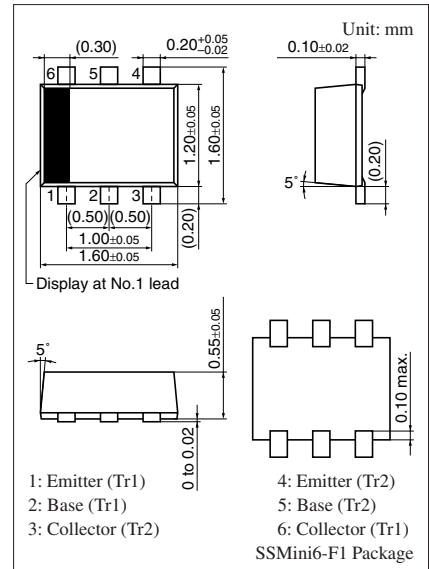
- Two elements incorporated into one package
(Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

■ Resistance by Part Number

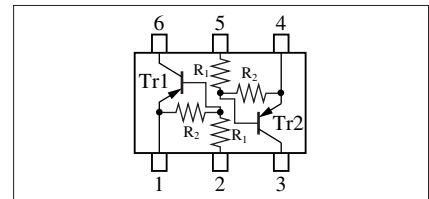
	Marking Symbol	(R ₁)	(R ₂)
• UP04111	9U	10 kΩ	10 kΩ
• UP04113	6S	47 kΩ	47 kΩ
• UP04116	6U	4.7 kΩ	—

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CB0}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I _C	-100	mA
Total power dissipation	P _T	125	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C



Internal Connection

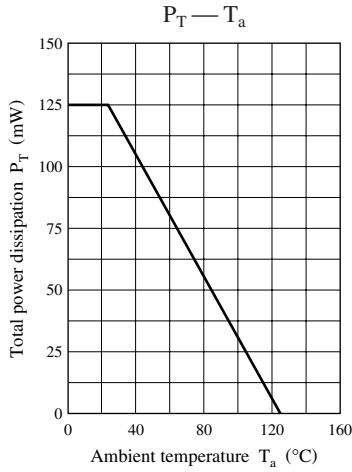


■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

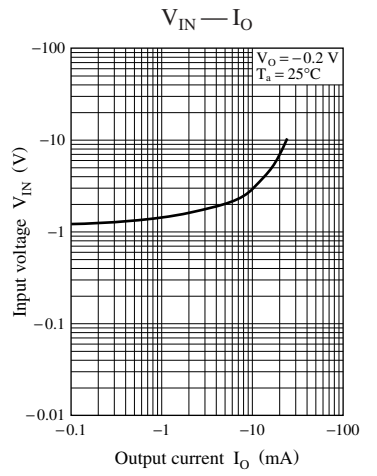
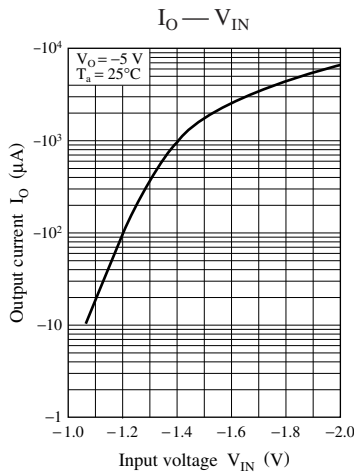
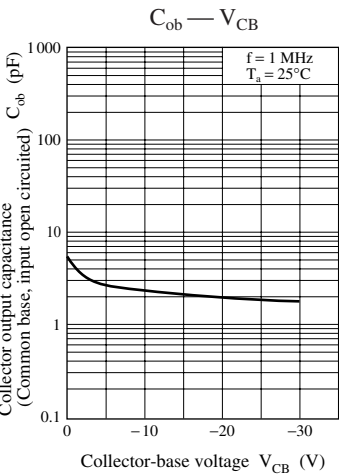
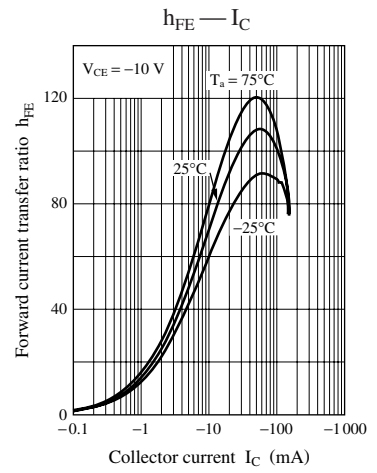
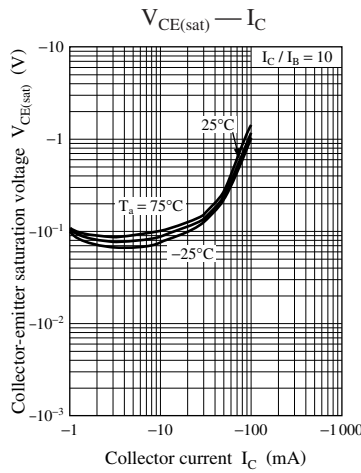
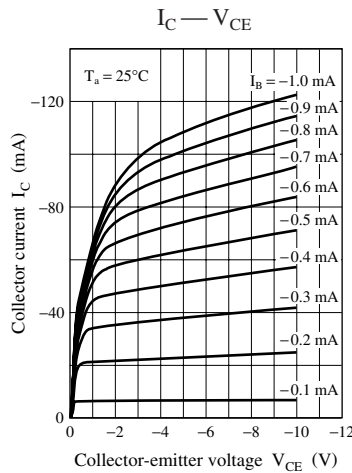
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -50 \text{ V}, I_B = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	UP04111	I_{EBO} $V_{EB} = -6 \text{ V}, I_C = 0$			-0.5	mA
	UP04113				-0.1	
	UP04116				-0.01	
Forward current transfer ratio	UP04111	h_{FE} $V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	35			—
	UP04113		80			
	UP04116		160		460	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			-0.25	V
Output voltage high-level	V_{OH}	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V_{OL}	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			-0.2	V
		$V_{CC} = -5 \text{ V}, V_B = -3.5 \text{ V}, R_L = 1 \text{ k}\Omega$				
Input resistance	UP04111	R_1	-30%	10	+30%	k Ω
	UP04113			47		
	UP04116			4.7		
Resistance ratio	UP04111	R_1 / R_2	0.8	1.0	1.2	—
	UP04113					
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

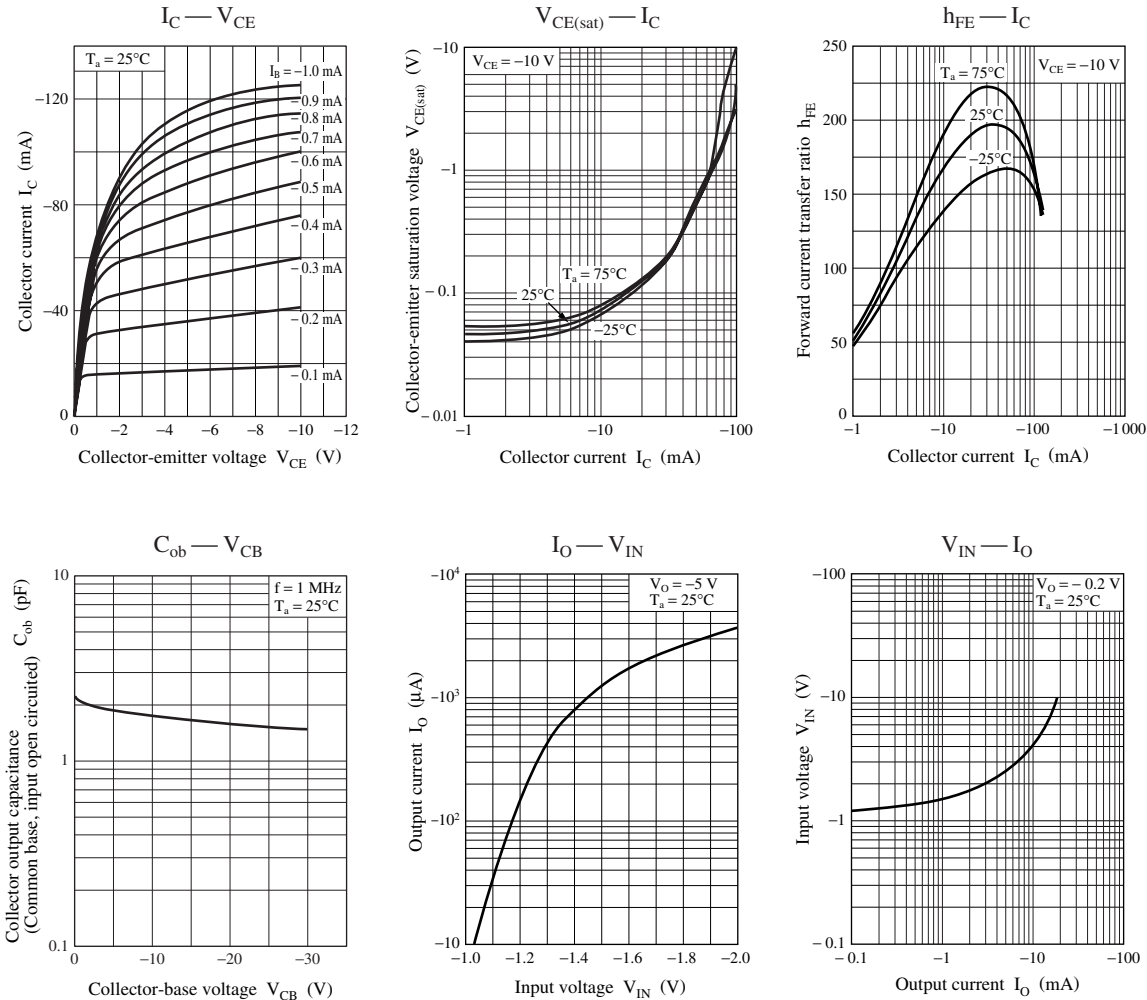
Common characteristics chart



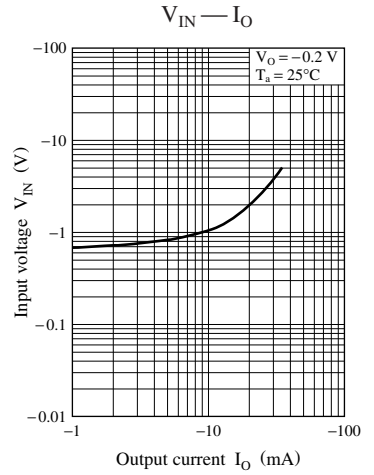
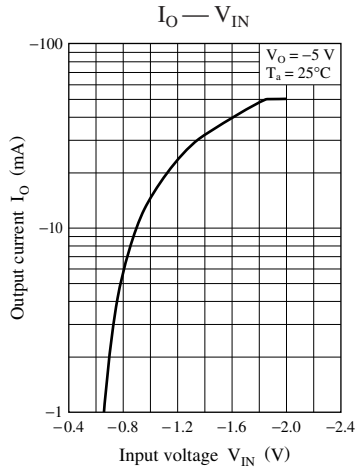
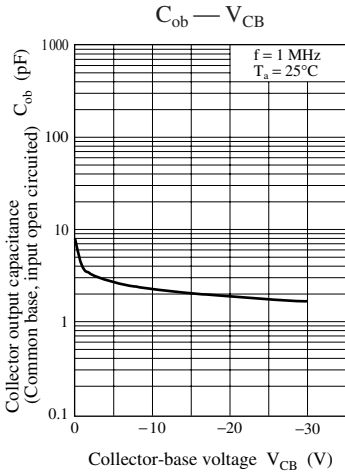
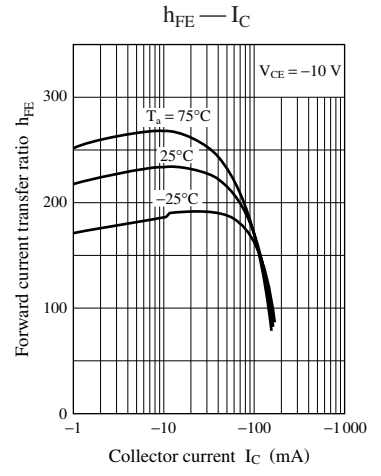
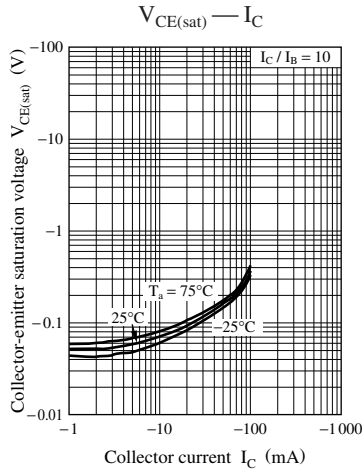
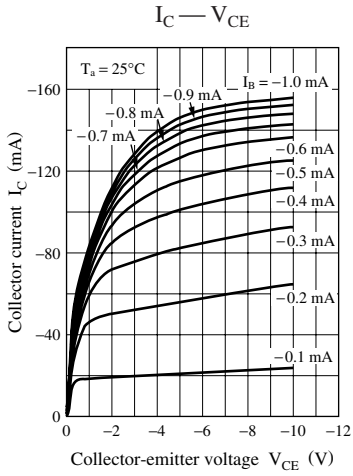
Characteristics charts of UP04111



Characteristics charts of UP04113



Characteristics charts of UP04116



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